

# 3/ Prel. Amend. A  
N. Ha  
1-16-02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Hirotooshi KUBO et al.**

Serial Number: **09/161,828**

Art Unit: **2814**

Filed: **September 29, 1998**

Examiner: **N. Ha**

For: **SEMICONDUCTOR DEVICE AND A METHOD OF FABRICATING THE SAME**

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

November 19, 2001

Sir:

Prior to continued examination on the merits, please amend the above-identified application as follows:

**IN THE SPECIFICATION:**

**Please amend specification as follows:**

**Please replace the paragraph beginning at page 6, line 11, with the following rewritten paragraph:**

As shown in Fig. 1, a first aspect of the present invention is a device of a semiconductor device, which comprises: a semiconductor substrate of a first conduction type; a drain layer of the first conduction type and formed on a surface layer of the semiconductor substrate; a gate insulating film formed in a partial region on the drain layer; a gate electrode formed on the gate insulating film;